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Large Excitonic Effects in the Optical Properties of Monolayer MoS_2

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The band structure and absorption spectrum of monolayer MoS_2 is calculated using the G_0W_0 approximation and the Bethe-Salpeter equation (BSE), respectively. We find that the so-called A and B peaks in the absorption spectrum arise from strongly bound excitons (0.7-0.8 eV) localized in distinct regions of the Brillouin zone and not from a split valence band as commonly assumed. Furthermore, we find the minimum band gap to be of the indirect type. This seems to conflict with recent experimental results showing stong luminescence in this material. However, our results indicate that the luminescence is a consequence of the large binding energy of the lowest exciton which stabilizes it against thermal relaxation.

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Nanostructured forms of the semi-conductor MoS_2 have recieved much attention due to their potential as catalysts for desulferization of crude oil and more recently for (photo)-electrochemical hydrogen evolution[1–3]. Bulk MoS_2 is composed of two-dimensional sheets held together by weak van der Waals forces and individual sheets can be isolated by exfoliation techniques similar to those used to produce graphene[4]. Single layers of MoS_2 therefore comprise highly interesting two-dimensional systems with a finite band gap and have recently been proposed for nano-electronics applications[5].

The optical properties of MoS_2 have been thoroughly studied experimentally [6–11]. The absorption spectrum shows two distinct low energy peaks at 1.88 eV and 2.06 eV, which are denoted by A and B respectively [12]. These features have traditionally been proposed to originate from direct transitions between a split valence band and the conduction band at the K point of the Brillouin zone. Their Rydberg satellites, Zeeman splitting, and dependence on crystal thickness have been investigated in detail [9]. Very recently, the quantum yield of luminescence from MoS_2 was shown to increase dramatically when the sample thickness was changed from a few layers to a monolayer [13, 14] and the results have been taken as an indication of a direct band gap in the single layer. This conjecture is supported by density functional theory (DFT) calculations, which indeed show a transition from indirect to direct gap when going from a few layers to monolayer MoS_2 [14–16]. However, while DFT has proven very successful in describing the ground state properties of a large variety of materials, it is not expected to provide a faithful description of excited state properties such as optical absorption and luminescence.

In this letter we present first-principles many-body perturbation theory calculations for the electronic structure of MoS_2. We show that monolayer MoS_2 has an indirect gap at the $K-T$ transition, which is ~ 0.5 eV smaller than the direct gap at K. The experimental absorption spectrum is reproduced by our calculations and it is shown that excitonic effects are very dominant due to the poor electronic screening in the two-dimensional layer. In particular, the A and B absorption peaks originate from two bound excitons located at different positions in the Brillouin zone and not from a split valence band originating from spin-orbit coupling and interlayer interactions as often stated in the literature [6]. This leads to a very different interpretation of the absorption spectra of MoS_2 and related dichalcogenides [12] and resolves the puzzle of why the double exciton is preserved in single layer structures, which do not have a split valence band[13, 14]. The high luminescence yield in monolayer MoS_2 can be attributed to the high binding energy (0.7 eV) of the A exciton, which strongly reduces the probability that excited electrons decay to the lowest point in the conduction band before recombining. In bilayer and bulk MoS_2 the difference between the direct and the indirect gap is larger and the exciton binding energies are lower, thus enhancing the probability for non-radiative decay of the excitons.

The many-body calculations described in this work were performed with the Yambo code[17] and the initial Kohn-Sham electronic structure was obtained with the DFT code ABINIT [18] using the LDA exchange-correlation functional, a plane wave cutoff of 500 eV, and a 45×45 k-point grid centered at the Γ point. We have used the experimental lattice constants for MoS_2 and for the single layer calculations the repeated layers were separated by 23 $\mathring{A}$, whereas we used a separation of 29.3 $\mathring{A}$ for the two layer calculations. For the one and two-layer calculations we used a Coulomb cutoff [19] in the direction perpendicular to the slabs to ensure convergence with respect to super cell size. The band structure was obtained within the G_0W_0 approximation [20] with a plane wave cutoff of 60 eV for the dielectric function, which ensures convergence of the gap to within 60 meV[28]. Unless stated otherwise the full frequency dependence of the response function has been taken into account. While the use of a plasmon-pole approxima-

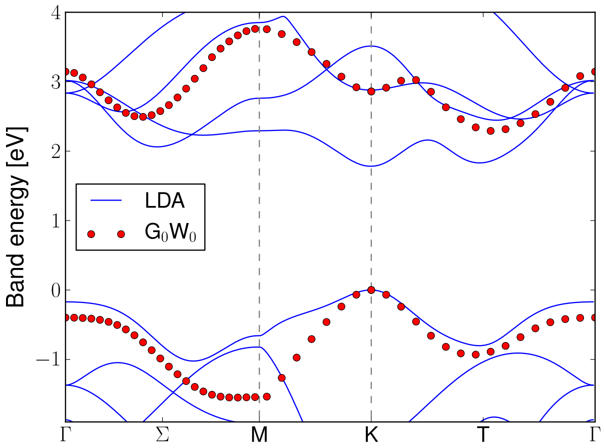

FIG. 1: (Color online). Band structure of single layer MoS_2. The Kohn-Sham band structure (blue lines) is seen to have a direct gap at K, whereas the QP band structure (red dots) has an indirect gap at the $K-T$ transition.

tion [21] only induces a slight increase of the band gap of $\sim$ 0.13 eV at the K point and 0.065 eV at the T point, these differences have consequences for the fine structure in the absorption spectrum. By assuming a static dielectric screening $\varepsilon(\mathbf{q},\omega) \sim \varepsilon(\mathbf{q},0)$, the Bethe-Salpeter Equation [22] can be recast into a two-particle excitonic Hamiltonian [23], which is diagonalized on a basis of electron-hole pairs. In this way the excitonic eigenstates can be expressed as a linear combination of single-particle transitions

$$|\lambda\rangle = \sum_{vck} A^{\lambda}_{vck}|vck\rangle, \tag{1}$$

where v, c, and k denote valence band, conduction band and Brillouin zone wave vector, respectively. The absorption spectrum is proportional to the imaginary part of the macroscopic dielectric function, which in the Tamm-Dancoff approximation can be written

$$\begin{aligned}\varepsilon_2(\omega) =& 2\pi \lim_{\mathbf{q}\to 0} v(\mathbf{q}) \sum_{\lambda} \delta(\omega - E_{\lambda}) \\ &\times \left| \sum_{vc\mathbf{k}} A^{\lambda}_{vck} \langle v\mathbf{k}-\mathbf{q}| e^{-i\mathbf{q}\cdot\mathbf{r}} |c\mathbf{k}\rangle \right|^2, \end{aligned} \tag{2}$$

where E_λ are the eigenvalues associated with $|\lambda\rangle$. For a single valence and conduction band, the coefficients $A_{vck} \equiv A(k)$ can be regarded as an excitonic k-space "wavefunction".

In Fig. 1, we show the quasi-particle (QP) band structure of single layer MoS_2 obtained within the G_0W_0 approximation as well as the LDA band structure. It is clear, that the inclusion of exchange and correlation at the G_0W_0 level, results in a severe modification of the band structure. The most prominent qualitative difference is the minimum gap. Whereas the LDA band structure shows a direct gap at the K-point of 1.8 eV, the G_0W_0 band structure has an indirect gap between K and T of 2.3 eV, which is 0.5 eV smaller than the minimum direct gap at K. Very often, the true QP band structure can be well approximated by the LDA band structure subject to a "scissors operator" which shifts the conduction bands by a k-independent constant to reproduce the correct gap. While such an approach has proven useful for a range of different semiconductors, it would certainly be a poor approximation in the present case.

The large direct band gap of 2.8 eV predicted by the G_0W_0 calculations may seem to be in conflict with the measured absorption spectrum of monolayer MoS_2 showing peaks at 1.9 eV and 2.1 eV. However, the QP particle band structure does not include the Coulomb attraction between the electron and the hole involved in optical excitations. In materials with low screening, the electron and hole may form strongly bound states leading to excitonic features in the absorption spectrum well below the QP band gap.

To include the effect of electron-hole interactions, we have solved the BSE and obtained the absorption spectrum resulting from light polarized in the MoS_2 plane. We have included the two highest valence bands and the four lowest conduction bands in the calculation (we have verified that the result does not change significantly when including more bands). The result is shown in Fig. 2. The inset shows the absorption spectrum calculated without electron-hole interactions. As expected from the

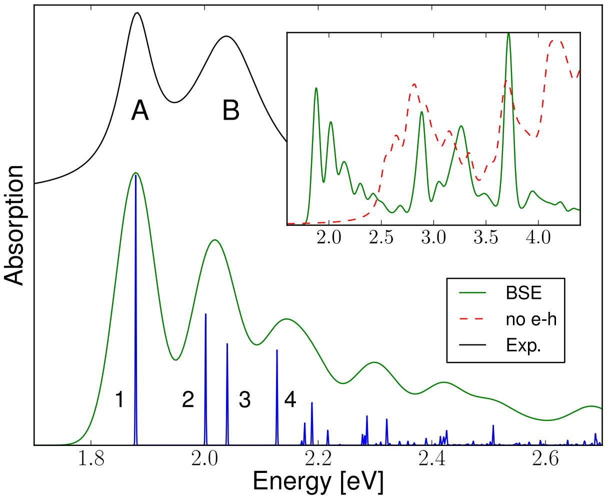

FIG. 2: (Color online). Absorption spectrum of single layer MoS_2 reproduced from the experiments in Ref. [13] (upper curve) and calculated from the BSE equation (lower curve). The calculated spectrum has been shifted down by 0.3 eV. The two peaks at 1.88 and 2.03 eV are identified with the A and B excitons. The inset shows the same BSE spectrum on a broader energy range along with absorption spectrum obtained directly from the G_0W_0 eigenvalues and LDA wave functions and with no electron-hole interaction included (red dashed curve).

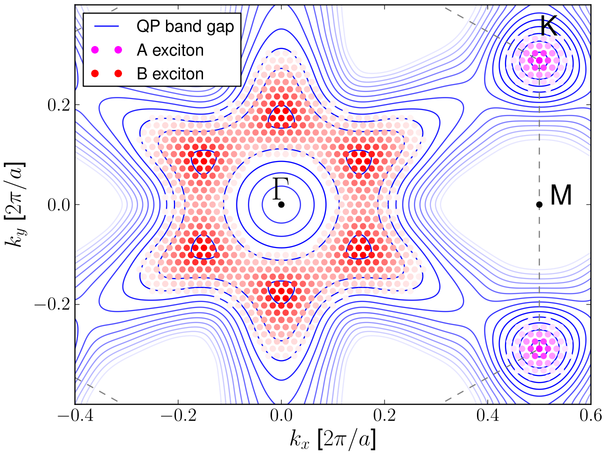

FIG. 3: (Color online). Contour plot of the direct quasiparticle gap of monolayer $\mathrm{MoS_2}$. The gap shows two distinct minima which support two excitonic states. One exciton (A) is centered at the global minimum at the K-point (QP gap ~ 2.8 eV) and the other exciton (B) is associated with a ring circling the Γ-point (QP gap ~ 3.1 eV). The two minima are well separated by a gap barrier of ~ 0.6 eV. The contours are separated by ~ 0.1 eV and the gray dashed line is the Brillouin zone boundary.

band structure it shows an absorption edge at ~ 2.8 eV corresponding to the direct QP band gap. However, when electron-hole interactions are included the absorption edge is lowered to ~ 2.1 eV, which is well below the direct gap. The energy difference of 0.7 eV is the result of strongly bound electron-hole pairs. Usually, such strong excitonic effects are only found in insulators with low dielectric constants, but in the present case it is the two-dimensional nature of a single $\mathrm{MoS_2}$ layer which confines the electron-hole pair and gives the large binding energy. Such large excitonic effects have also been observed in hexagonal BN [24, 25] and SiC [26], which show similar two-dimensional confinement. The main panel in Fig. 2 shows the low energy part of the calculated absorption spectrum which has been shifted downward by 0.3 eV for comparison with experiment (black curve).It is seen to have four distinct peaks at low energies. The first of these is identified with the A exciton and peaks 2 and 3 comprise the B exciton. In contrast to peaks 1-3, the fourth peak changes its weight and position when we increase the k-point sampling and although the peak seems to become less significant at high k-point samplings we have not been able to fully converge this feature in the spectrum.

To demonstrate the nature of the peaks we can plot the magnitude of the expansion coefficients $|A^{A,B}(k)|^2$ appearing in Eq. 1 as a function of Brillouin zone coordinates. This is shown in Fig. 3 for peak 1 and peak 3 (A and B excitons) along with contour lines indicating the direct QP gap. Peak 2 has nearly identical weights as peak 3 but has an additional small weight near K. The QP gap has a global minimum situated at the K-point and a well defined local minimum located in a ring defined roughly by $|k| \sim |K|/3$. These minima are seen to support the A and B excitons. The expansion coefficients also allow us to calculate the exact binding energy of the two excitons. Using that the exciton energy without the e-h interaction is $E^{QP}_{A,B} = \sum_k |A^{A,B}(k)|^2(\varepsilon^{QP}_{ck} - \varepsilon^{QP}_{vk})$ we find that the binding energy of the A and B excitons are 0.7 eV and 0.8 eV, respectively. The slightly larger binding energy of the B exciton agrees with the fact that it is more delocalized in the Brillouin zone and thereby more localized in real space resulting in stronger coulomb interaction between the electron and hole. Equivalently, we may say that the A exciton has a smaller hydrogenic binding energy due to its smaller effective mass resulting from the high "gap curvature" at the K-point. In fact, we may estimate the value of the exciton binding energy as $E^{3D}_b = m_e/2\varepsilon_r^2$ where E^{3D}_b is the binding energy in atomic units, m_e the exciton effective mass, and ε_r the dielectric constant. We have calculated ε_r within the random phase approximation and obtain $\varepsilon_\parallel = 4.1$ and $\varepsilon_\perp = 1.4$ for parallel and orthogonal polarization respectively. The exciton effective mass at K is 0.42 which gives $E^{3D}_b = 0.32$ eV for the parallel component of ε_r. However, since the exciton is confined in a nearly two-dimensional region, it may be more reasonable to consider a two-dimensional hydrogen model, which gives $E^{2D}_b = 4E^{3D}_b = 1.3$ eV [27]. While, such estimates are not reliable for detailed quantitative analysis, the hydrogen model does give the right order of magnitude for the binding energy and the BSE value of 0.7 eV is close to the average value of the two-dimensional and three-dimensional models.

The recently measured high luminescence yield in monolayer $\mathrm{MoS_2}$ [13, 14], seem to be in conflict with the $\mathrm{G_0W_0}$ band structure shown in Fig. 1. This is because the indirect gap suggests that electrons excited at K would relax to the T point by phonon scattering from which point they would not be able to recombine directly with the hole left at K. This picture is, however, based on the QP bands and do not take the strong binding energy of the electron-hole pairs into account. Indeed, the energy of the A exciton is 0.2 eV lower than that of a free hole at K and a free electron at T (since the indirect gap is only 0.5 eV below the direct gap). Even if the binding energy of the indirect exciton, consisting of a $K-T$ electron-hole pair, is comparable to that of the direct exciton at K, luminescence could still take place if the nonradiative relaxation of the exciton is slow compared to the recombination time. This is not an unreasonable assumption since the downhill relaxation of the exciton requires that the coherence between the electron and hole is conserved during the electron-phonon scattering events. Therefore, we propose that the high luminescence yield in monolayer $\mathrm{MoS_2}$ is the result of strong excitonic binding energies and associated low relaxation rates, rather

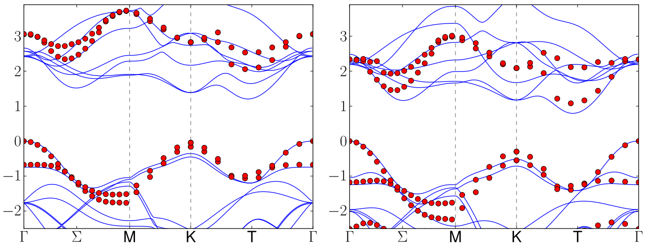

FIG. 4: (Color online). Left: Band structure bilayer MoS_2. Right: Band structure of bulk MoS_2. The blue lines are the Kohn-Sham band structure and the dots are G_0W_0 band structure.

than a direct band gap as previously suggested[13, 14].

For comparison we have also calculated the band structure and absorption spectrum of bulk and bilayer MoS_2. We find quantitative differences from monolayer MoS_2 which are expected to lower the quantum yield of luminescence. To illustrate this, we show the band structure of bulk and bilayer MoS_2 in Fig. 4. The results were obtained with a 30×30 k-point sampling, and the bulk band structure was calculated using the plasmon pole approximation. For the bilayer (bulk), the indirect gap is 0.8 eV (0.9 eV) lower than the direct gap. The same value is only 0.5 eV for the monolayer. Furthermore, in the bulk material the screening is much larger than in mono- and bilayer structures and the exciton binding energies are less than 0.1 eV. Consequently, the phonon mediated scattering of the photo excited excitons from the direct to the indirect gap should be more effective in bilayer and bulk structures in agreement with the fact that no or very low luminescence is observed in these materials.

In conclusion, we have performed first-principles calculations on MoS_2 and shown that both monolayer and multilayer structures have an indirect band gap. We propose that the recently observed high quantum yield of luminescence in monolayer MoS_2 can be attributed to the large exciton binding energies leading to low thermal relaxation rates. Our results show that the quasiparticle band gap obtained with the G_0W_0 approximation is qualitatively different from the LDA band structure and leads to a very different interpretation of absorption and luminescence spectra. In particular, the A and B peaks in the absorption spectrum are not associated with a valence band split by interlayer interactions but rather is due to two distinct, strongly bound excitons.

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[28] We have tested convergence for a 15×15 k-point sampling by increasing the cutoff energy to 250 eV for the response function empty states, correlation energy empty states, and plane waves.